Silicon Carbide Schottky Diode

1700 V, 10 A

NDSH10170A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 361 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- These Devices are Halogen Free/BFR Free and are RoHS Compliant

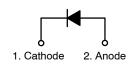
Applications

- SMPS, Solar Inverter, UPS
- Power Switching Circuits



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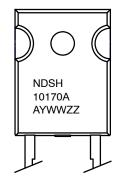


Schottky Diode



TO-247-2LD CASE 340DA

MARKING DIAGRAM



NDSH10170A

= Specific Device Code

YWW

77

1

= Assembly Plant Code= Date Code (Year & Week)

= Lot Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS ($T_J = 25$ °C unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage		1700	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		361	mJ
lF	Continuous Rectified Forward Current @ T _C < 157°C		10	Α
	Continuous Rectified Forward Current @ T _C < 135°C		16	
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	868	Α
		T _C = 150°C, 10 μs	798	Α
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	105	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	25	Α
Ptot	Power Dissipation	T _C = 25°C	185	W
		T _C = 150°C	31	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. E_{AS} of 361 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 38 A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Symbol Parameter		Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.81	°C/W
R _{θJA} Thermal Resistance, Junction to Ambient, Max		40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 10 A, T _J = 25°C	-	1.50	1.75	V
		I _F = 10 A, T _J = 125°C	_	1.87	-	
		I _F = 10 A, T _J = 175°C	-	2.19	-	
I _R	Reverse Current	V _R = 1700 V, T _J = 25°C	-	0.09	40	μΑ
		V _R = 1700 V, T _J = 125°C	-	0.42	60	
		V _R = 1700 V, T _J = 175°C	-	2.46	100	
Q _C	Total Capacitive Charge	V = 800 V	-	74	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	856	-	pF
		V _R = 400 V, f = 100 kHz	-	69	-	
		V _R = 800 V, f = 100 kHz	-	48	_	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping	
NDSH10170A	NDSH10170A	TO-247-2LD (Pb-Free / Halogen Free)	30 Units / Tube	

TYPICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

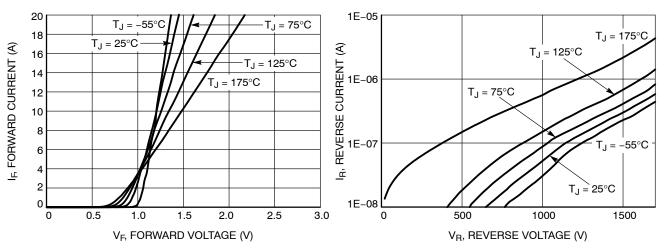


Figure 1. Forward Characteristics

Figure 2. Reverse Characteristics

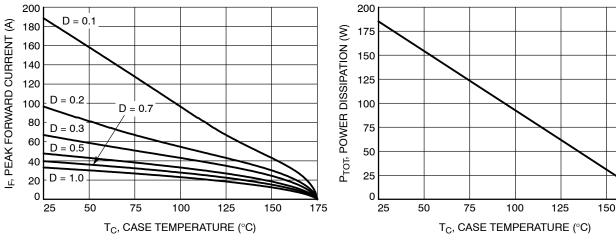


Figure 3. Current Derating

Figure 4. Power Derating

175

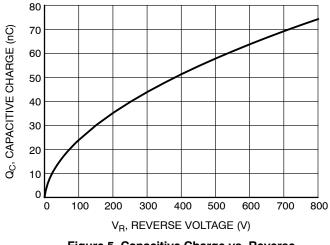


Figure 5. Capacitive Charge vs. Reverse Voltage

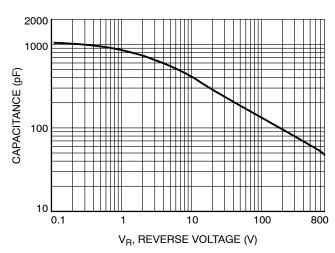


Figure 6. Capacitive vs. Reverse Voltage

TYPICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

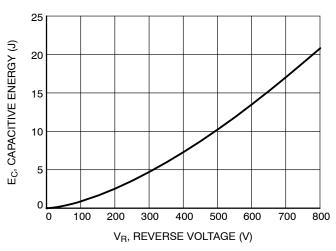


Figure 7. Capacitance Stored Energy

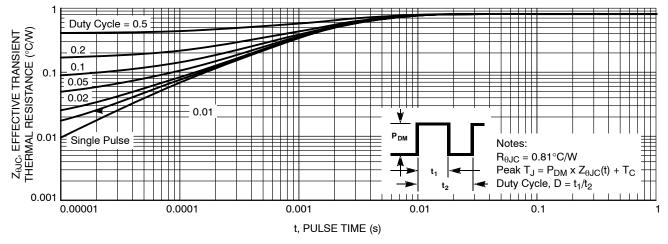
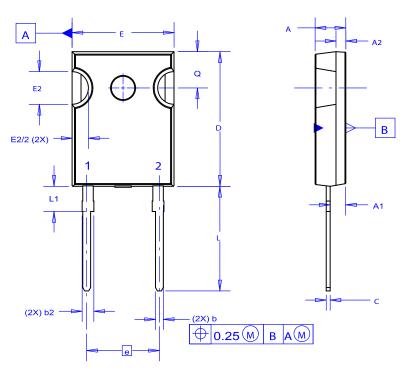


Figure 8. Junction-to-Case Transient Thermal Response Curve

PACKAGE DIMENSIONS

TO-247-2LD CASE 340DA **ISSUE A**

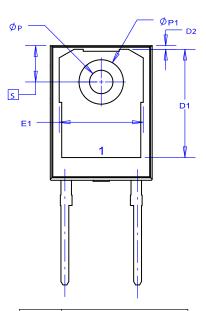


NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.

 B. ALL DIMENSIONS ARE IN MILLIMETERS.

- C. DRAWING CONFORMS TO ASME Y14.5 2009.
 D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



DIM	MILLIMETERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.53	1.65	1.77		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	?	~		
D2	0.51	0.93	1.35		
Е	15.37	15.62	15.87		
E1	12.81	l	~		
E2	4.96	5.08	5.20		
е	?	11.12	?		
L	15.75	16.00	16.25		
L1	3.69	3.81	3.93		
ØΡ	3.51	3.58	3.65		
ØP1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

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